



60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(on)}	I _D T _A = +25°C
-60V	$150 m\Omega$ @ $V_{GS}= -10V$	-3A
-60 V	185mΩ @ V _{GS} = -4.5V	-2.7A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) test in production
- Low on-resistance
- Fast switching speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

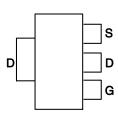
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 3
- Weight: 0.112 grams (Approximate)

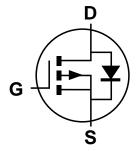
SOT223



Top View



Pin Out - Top



Equivalent Circuit

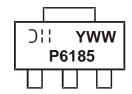
Ordering Information (Note 5)

Part Number	Case	Packaging
DMP6185SEQ-13	SOT223	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Dil = Manufacturer's Marking
P6185 = Marking Code
YWW or \overline{Y}WW = Date Code Marking
Y or \overline{Y} = Year (ex: 7 = 2017)
WW = Week (01 - 53)



Characteristic	Symbol	Value	Unit		
Drain-Source voltage	V_{DSS}	-60	V		
Gate-Source voltage		V_{GS}	±20	V	
Continuous Drain surrent (Note 7) // 401/	T _A = +25°C	1	-3	A	
Continuous Drain current (Note 7) V _{GS} = -10V	$T_A = +70$ °C	ID	-2.4		
Maximum Body Diode Continuous Current		Is	-2	A	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I _{DM}	-15	A	
Single Pulsed Avalanche Current (Note 8)		I _{AS}	-16	A	
Single Pulsed Avalanche Energy (Note 8)		Eas	13	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	D	1.2	W
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_{D}	0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	D	104	- °C/W
Thermal Resistance, Junicilon to Ambient (Note 0)	t<10s	$R_{\theta JA}$	51	
Total Power Dissipation (Note 7)	$T_A = +25^{\circ}C$	ь	2.2	- W
Total Power Dissipation (Note 1)	$T_A = +70^{\circ}C$	P_{D}	1.4	
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	0	60	°C/W
Thermal Resistance, Juniction to Ambient (Note 1)	t<10s	$R_{\theta JA}$	30	
Thermal Resistance, Junction to Case (Note 7)	R ₀ JC	7.6		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

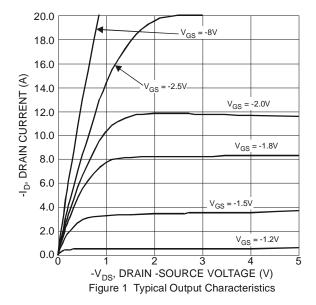
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	-	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	=	-	-1	μA	$V_{DS} = -48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)			l			1 22	
Gate Threshold Voltage	V _{GS(th)}	-1	-	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance			110	150	0	$V_{GS} = -10V, I_D = -2.2A$	
Static Drain-Source On-Resistance	R _{DS} (ON)	-	130	185	mΩ	$V_{GS} = -4.5V, I_D = -1.8A$	
Diode Forward Voltage	V _{SD}	-	-0.75	-0.95	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)			•				
Input Capacitance	C _{iss}	=	708	=	pF	201/ 1/ 01/	
Output Capacitance	Coss	_	39	_	pF	$V_{DS} = -30V, V_{GS} = 0V,$	
Reverse Transfer Capacitance	C _{rss}	_	32	-	pF	f = 1MHz	
Gate Resistance	Rg	_	17	28	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	-	6.2	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	-	14	-	nC	201/ 1 101	
Gate-Source Charge	Q _{gs}	-	2.8	-	nC	$V_{DS} = -30V, I_{D} = -12A$	
Gate-Drain Charge	Q _{gd}	_	3.1	-	nC	1	
Turn-On Delay Time	t _{D(on)}	-	5.2	-	ns		
Turn-On Rise Time	t _r	=	23	=	ns	$V_{DS} = -30V, R_{L} = 2.5\Omega$	
Turn-Off Delay Time	t _{D(off)}	-	33	-	ns	$V_{GS} = -10V$, $R_G = 3\Omega$	
Turn-Off Fall Time	t _f	=	39	=	ns		
Body Diode Reverse Recovery Time	t _{rr}	-	22	-	ns		
Body Diode Reverse Recovery Charge	Q _{rr}	-	17	-	nC	I _F = -12A, di/dt = 100A/μs	

Notes

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 8. UIS in production with L = 0.1mH, starting $T_A = +25$ °C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.





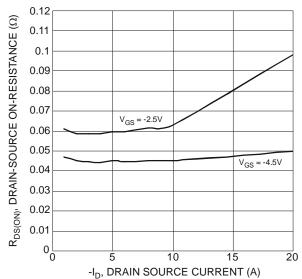
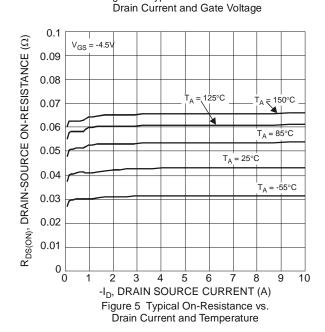
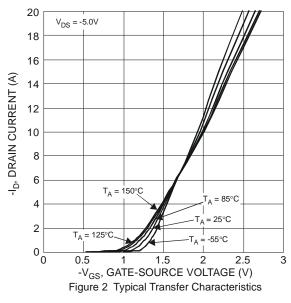
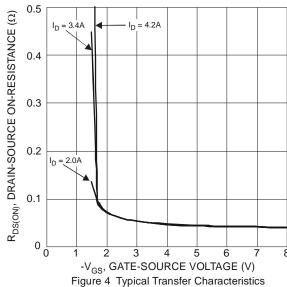
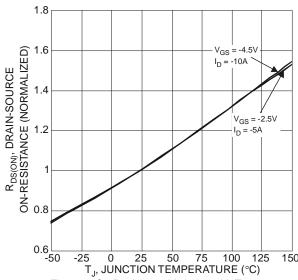


Figure 3 Typical On-Resistance vs.











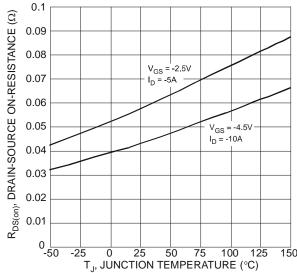
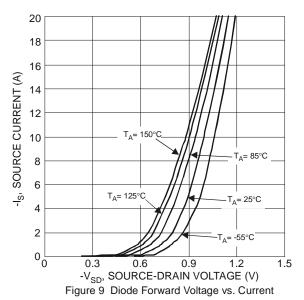
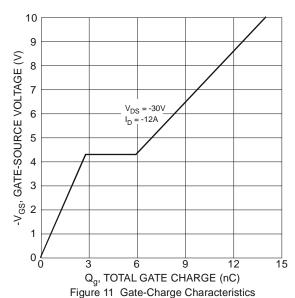


Figure 7 On-Resistance Variation with Temperature





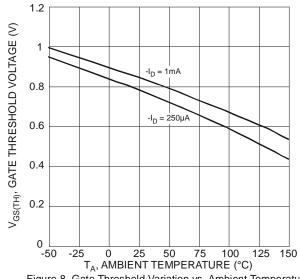
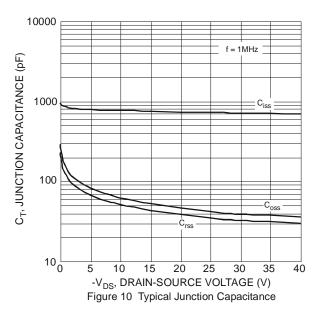
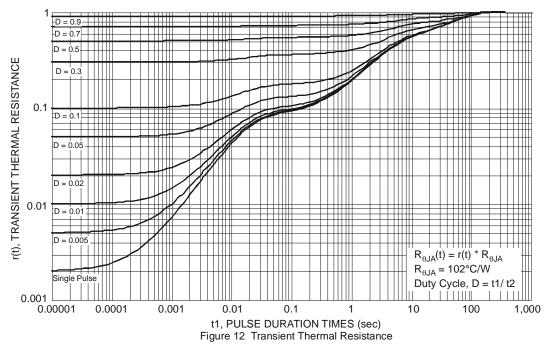


Figure 8 Gate Threshold Variation vs. Ambient Temperature

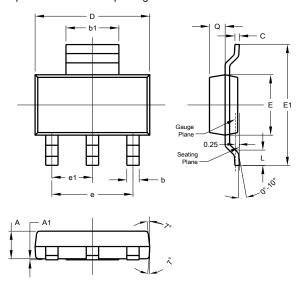






Package Outline Dimensions

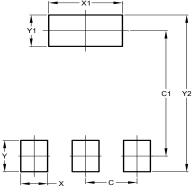
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1	_	_	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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